

S/N 10/028643

PATENT



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Kie Y. Ahn et al. Examiner: Long Pham  
Serial No.: 10/028,643 Group Art Unit: 2814  
Filed: December 20, 2001 Docket: 1303.030US1  
Title: LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO<sub>3</sub>  
GATE DIELECTRICS

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**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

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By their Representatives,

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By



David C. Peterson

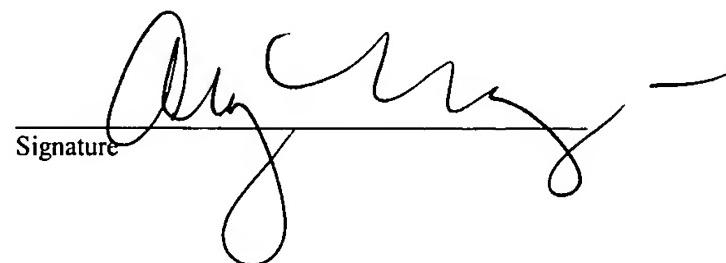
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 10<sup>th</sup> day of February, 2004.

Name

Amy Moriarty

Signature



Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(Use as many sheets as necessary)</i>		Complete if Known Application Number      10/028,643 Filing Date      December 20, 2001 First Named Inventor      Ahn, Kie Group Art Unit      2814 Examiner Name      Pham, Long				
 Sheet 1 of 4		Attorney Docket No: 1303.030US1				

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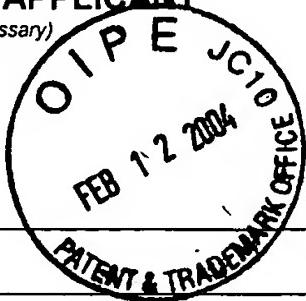
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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Complete if Known

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<b>Filing Date</b>	December 20, 2001		
<b>First Named Inventor</b>	Ahn, Kie		
<b>Group Art Unit</b>	2814		
<b>Examiner Name</b>	Pham, Long		

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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<p>Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)</p> <p style="text-align: center;"><i>O P E J C 10</i></p> <p style="text-align: center;"><i>FEB 1 2 2004</i></p> <p style="text-align: center;"><i>PATENT &amp; TRADEMARK OFFICE</i></p>	<p><i>Complete if Known</i></p> <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>10/028,643</td> </tr> <tr> <td>Filing Date</td> <td>December 20, 2001</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>2814</td> </tr> <tr> <td>Examiner Name</td> <td>Pham, Long</td> </tr> </table>	Application Number	10/028,643	Filing Date	December 20, 2001	First Named Inventor	Ahn, Kie	Group Art Unit	2814	Examiner Name	Pham, Long
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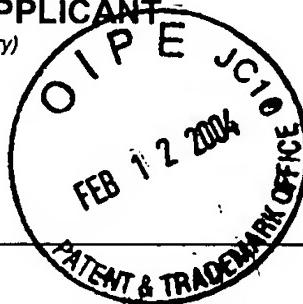
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